Octal Bus Transceivers (with inverted 3-state outputs)
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HITACHI

Description

This octal bus transceiver is designed for asynchronous two-way communication between data buses. The control fuction implementation allows for maximum flexibility in timing.

This device allows data transmission from the A bus to the B bus or from the B bus to the A bus depending upon the logic levels at the enable inputs (\overline{GBA} and \overline{GAB}).

The enable inputs can be used to disable the device so that the buses are effectively isolated.

The dual-enable configuration gives these devices the capability to store data by simultaneous enabling of $\overline{\text{GBA}}$ and GAB. Each output reinforces its input in this transceiver configuration. Thus, when both control inputs are enabled and all other data sources to the two sets of bus lines are at high impedance, both sets of bus lines (16 in all) will remain at their last states. The 8-bit codes appearing on the two sets of buses will be identical for the HD74HC623 or coplementary for the HD74HC620.

Features

• High Speed Operation: t_{pd} (Bus to Bus) = 12 ns typ ($C_L = 50 \text{ pF}$)

• High Output Current: Fanout of 15 LSTTL Loads

• Wide Operating Voltage: $V_{CC} = 2$ to 6 V

• Low Input Current: 1 µA max

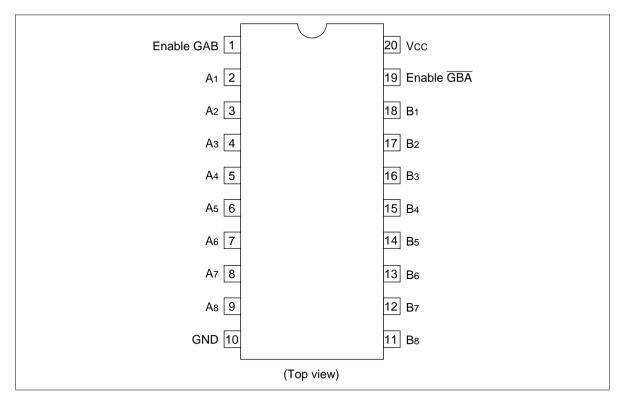
• Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)

Function Table

Enable Inputs Operation **GBA** GAB HD74HC620 **HD74HC623** B data to A bus L B data to A bus A data to B bus Н Н A data to B bus Н L Isolation Isolation Н \overline{B} data to A bus, \overline{A} data to B bus L B data to A bus, A data to B bus



Pin Arrangement

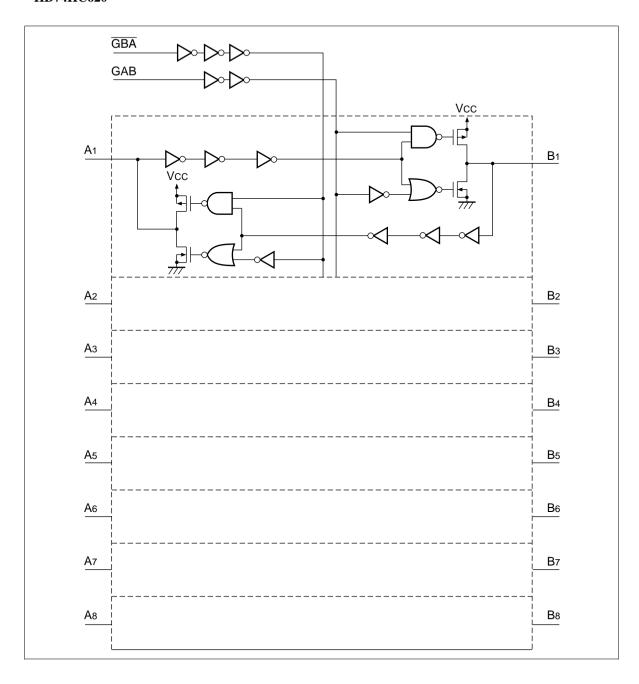


Absolute Maximum Ratings

Item	Symbol	Rating	Unit	
Supply voltage range	V _{cc}	-0.5 to +7.0	V	
Input voltage	V_{IN}	-0.5 to V_{cc} + 0.5	V	
Output voltage	V _{out}	-0.5 to $V_{cc} + 0.5$	V	
Output current	I _{OUT}	±35	mA	
DC current drain per V _{cc} GND	I _{CC} , I _{GND}	±75	mA	
DC input diode current	I _{IK}	±20	mA	
DC output diode current	I _{ok}	±20	mA	
Power Dissipation per package	P _T	500	mW	
Storage temperature	Tstg	-65 to +150	°C	

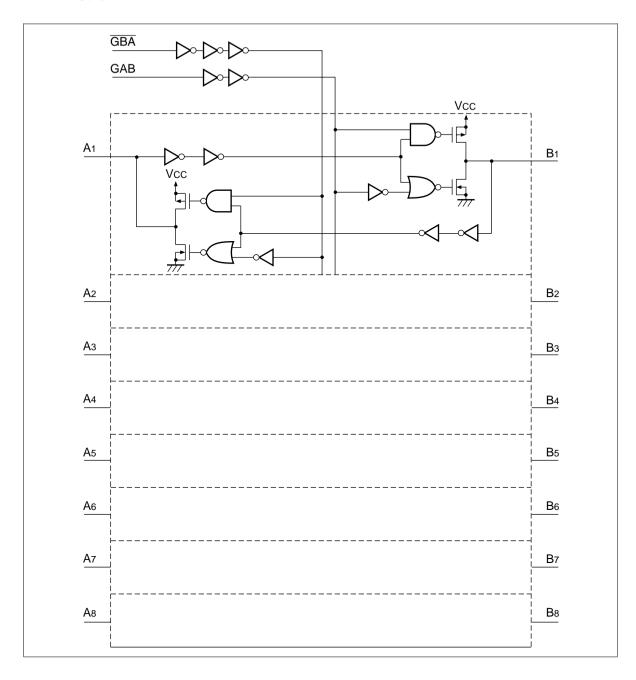
Block Diagram

HD74HC620



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HD74HC623



DC Characteristics

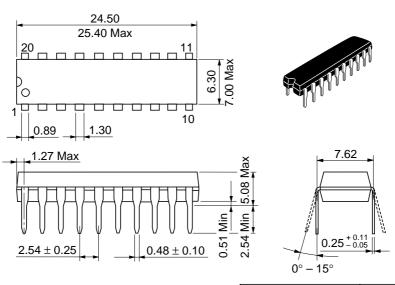
			Ta =	: 25°(:	Ta = - +85°C	-40 to			
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Condition	ns
Input voltage	V _{IH}	2.0	1.5	_	_	1.5	_	V		
		4.5	3.15	_	_	3.15	_			
		6.0	4.2	_	_	4.2	_	_		
	V _{IL}	2.0	_	_	0.5	_	0.5	V		
		4.5	_	_	1.35	_	1.35	_		
		6.0	_	_	1.8	_	1.8	=		
Output voltage	V _{OH}	2.0	1.9	2.0	_	1.9	_	V	Vin = V _{IH} or V _{IL}	I _{OH} = -20 μA
		4.5	4.4	4.5	_	4.4	_	_		
		6.0	5.9	6.0	_	5.9	_	=		
		4.5	4.18	_	_	4.13	_	_		$I_{OH} = -6 \text{ mA}$
		6.0	5.68	_	_	5.63	_	_		$I_{OH} = -7.8 \text{ mA}$
	V _{OL}	2.0	_	0.0	0.1	_	0.1	V	$Vin = V_{IH} \text{ or } V_{IL}$	I _{OL} = 20 μA
		4.5	_	0.0	0.1	_	0.1	_		
		6.0	_	0.0	0.1	_	0.1	_		
		4.5	_	_	0.26	_	0.33	=		I _{OL} = 6 mA
		6.0	_	_	0.26	_	0.33	_		I _{OL} = 7.8 mA
Off-state output current	I _{oz}	6.0	_	_	±0.5	_	±5.0	μΑ	$Vin = V_{IH} \text{ or } V_{IL}$ $Vout = V_{CC} \text{ or } C$	
Input current	lin	6.0	_	_	±0.1	_	±1.0	μΑ	Vin = V _{CC} or GN	ND
Quiescent supply current	I _{cc}	6.0	_	_	4.0	_	40	μΑ	Vin = V _{cc} or Gf	ND, lout = $0 \mu A$

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

	Ta = -40 to
Га = 25°С	+85°C

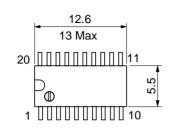
Item	Symbol	v ^^	Min	Typ	Max	Min	May	Unit	Test Conditions
Item	Symbol	V _{cc} (V)	IVIIII	тур	IVIAX	IVIIII	IVIAX	Ullit	rest Conditions
Propagation delay	$t_{\tiny PLH}$	2.0	_	_	100	_	125	ns	
time	$t_{\tiny PHL}$	4.5	_	12	20	_	25		
		6.0	_	_	17	_	21	_	
Output enable	t _{zH}	2.0	_	_	150	_	190	ns	
time	$\mathbf{t}_{\scriptscriptstyle ZL}$	4.5	_	12	30	_	38	-	
		6.0	_	_	26	_	33	_	
Output disable	t _{HZ}	2.0	_	_	150	_	190	ns	
time	t_{LZ}	4.5	_	16	30	_	38		
		6.0	_	_	26	_	33	_	
Output rise/fall	t _{TLH}	2.0	_	_	60	_	75	ns	
time	$t_{\scriptscriptstyle THL}$	4.5	_	4	12	_	15		
		6.0	_	_	10	_	13	=	
Input capacitance	Cin	_	_	5	10	_	10	pF	

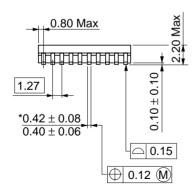
Unit: mm

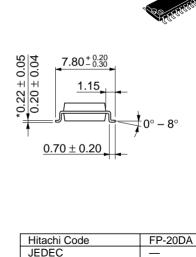


Hitachi Code	DP-20N
JEDEC	_
EIAJ	Conforms
Weight (reference value)	1.26 g

Unit: mm







Weight (reference value)

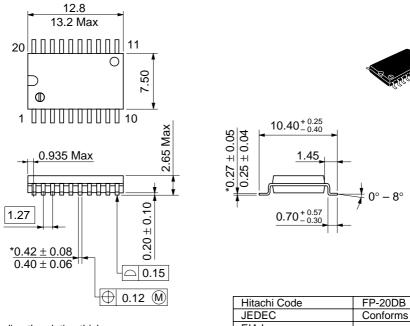
Conforms

0.31 g

EIAJ

*Dimension including the plating thickness
Base material dimension

Unit: mm



*Dimension including the plating thickness

Base material dimension

*EIAJ

Weight (reference value) 0.52 g

Cautions

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